

AMENDMENTS TO THE SPECIFICATION

Page 3, lines 8-20, amend the paragraph as follows:

Thus, to form a silicon device having higher performance, research has ~~researches have been done in which on such a technology that~~ a device such as a thin-film transistor made of single-crystal silicon thin film is formed in advance, and then a semiconductor device is manufactured by bonding this thin-film transistor on an insulating substrate (e.g. WO93/15589 (published on August 5, 1993), J.P. Salerno, "Single Crystal Silicon AMLCDs", Conference Record of the 1994 International Display Research Conference (IDRC) P.39-44(1994), and Q.-Y. Tong & U. Gesele, "SEMICONDUCTOR WAFER BONDING: SCIENCE AND TECHNOLOGY", John Wiley & Sons, New York(1999)).

Page 7, lines 22-25, amend the paragraph as follows:

To solve this problem, a device using single-crystal silicon has been developed, in parallel with research ~~researches~~ for further homogenization and improvement of crystallinity of polycrystalline silicon.

Page 35, lines 18-24, amend the paragraph as follows:

Although the gate electrodes 12 are made of a heavily-doped polysilicon silicon film and W silicide, the gate

electrodes 12 may be solely ~~solely~~ made of polycrystalline silicon or made of other types of high melting point metal or silicide, and the materials are selected in accordance with a required level of electrical resistance and heat resistance.

Pages 41-42, amend the paragraph bridging these pages from page 41, line 24 to page 42, line 15, as follows:

More specifically, after a part of the CMOS process is carried out in advance in a typical IC manufacturing line, i.e. after the gate electrodes 12, gate insulating film 13, protective insulating film, and planarized film (BPSG) are formed and implantation of impurity ions ( $\text{BF}_3^+$ ,  $\text{P}^+$ ) to the source and drain is carried out, the planarization is performed by CMP (Chemical-Mechanical Polishing). Subsequently, a  $\text{SiO}_2$  film which is 10nm thick is formed, and the single-crystal silicon substrate 10a having a dense position 15 of implanted hydrogen ions, to which hydrogen ions, a dose ~~dose~~-amount of  $5 \times 10^{16}/\text{cm}^2$ , are implanted with a predetermined energy is formed. Then these members are reshaped so as to have predetermined sizes corresponding to the formation area on the insulating substrate 2. Note that, at the dense position 15 of implanted hydrogen ions, the concentration of hydrogen ions is at the maximum.